

10V Drive Nch MOSFET

RCX120N25

Structure

Silicon N-channel MOSFET

Features

- 1) Low on-resistance.
- 2) High speed switching.
- 3) Gate-source voltage V_{GSS} garanteed to be $\pm 30 \text{V}$
- 4) High Power Package (TO-220FM).

• Dimensions (Unit : mm) TO-220FM

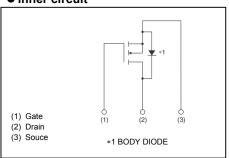
Application

Switching

Packaging specifications

- 1 dottagning opcomoducione					
	Package	Bulk			
Type	Code	-			
	Basic ordering unit (pieces)	500			
RCX120N25		0			

• Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	250	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	Continuous	I _D *3	±12	Α
	Pulsed	I _{DP} *1	±48	Α
Source current	Continuous	l _s *3	12	Α
(Body Diode)	Pulsed	I _{SP} *1	48	Α
Avalanche current		I _{AS} *2	6	Α
Avalanche energy		E _{AS} *2	10.5	mJ
Power dissipation(Tc=25°C)		P_{D}	40	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	Rth (ch-c)*	3.125	°C / W

^{*} T_C=25°C

^{*2} L= 500 μ H, V_{DD}=50V, R_G=25 Ω , T_{ch}=25 $^{\circ}$ C

^{*3} Limited only by maximum channel temperature allowed.

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±100	nA	$V_{GS}=\pm30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	1	1	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	1	10	μA	V _{DS} =250V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	3	1	5	٧	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	R _{DS (on)} *	-	180	235	mΩ	I _D =6A, V _{GS} =10V
Forward transfer admittance	I Y _{fs} I*	3.25	1	1	S	I _D =6A, V _{DS} =10V
Input capacitance	C _{iss}	1	1800	-	pF	V _{DS} =25V
Output capacitance	C _{oss}	1	100	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	60	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	33	-	ns	I _D =6A, V _{DD} ≒125V
Rise time	t _r *	1	65	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	1	45	-	ns	R_L =20.83 Ω
Fall time	t _f *	1	20	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	35	-	nC	I _D =12A,
Gate-source charge	Q _{gs} *	-	15	-	nC	V _{DD} ≒125V
Gate-drain charge	Q _{gd} *	-	12	-	nC	V _{GS} =10V

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.5	V	I _s =12A, V _{GS} =0V

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

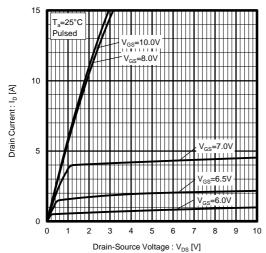


Fig.3 Typical Transfer Characteristics

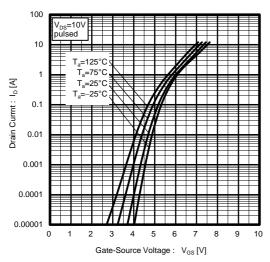


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

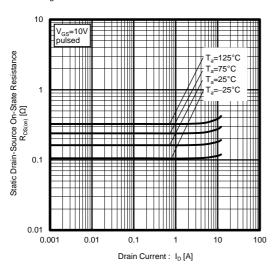


Fig.2 Typical Output Characteristics (II)

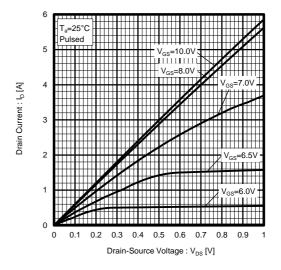


Fig.4 Gate Threshold Voltage vs. Channel Temperature

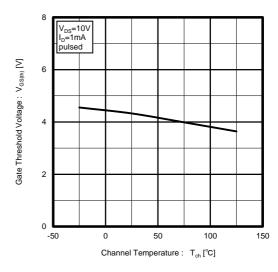


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

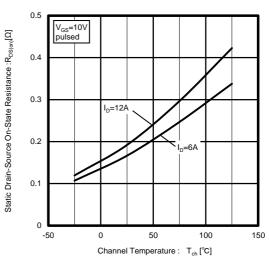


Fig.7 Forward Transfer Admittance vs. Drain Current

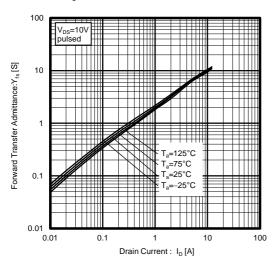


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

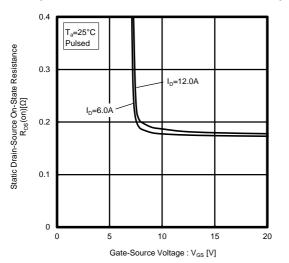


Fig.11 Dynamic Input Characteristics

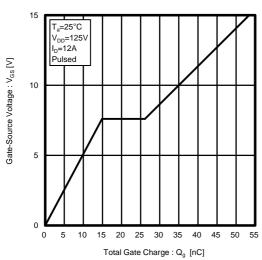


Fig.8 Source Current vs. Source-Drain Voltage

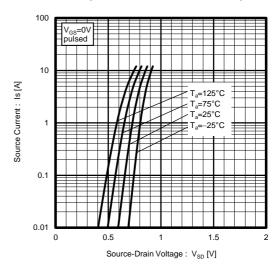


Fig.10 Switching Characteristics

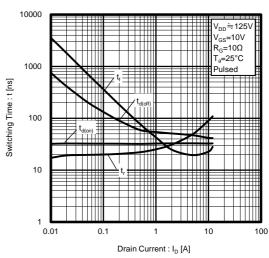


Fig.12 Typical Capacitance vs. Drain-Source Voltage

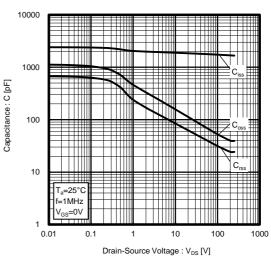
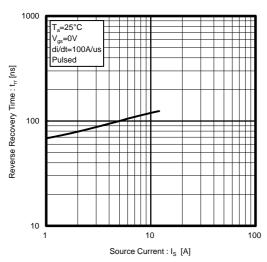
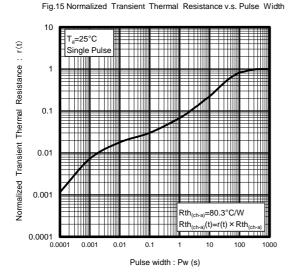
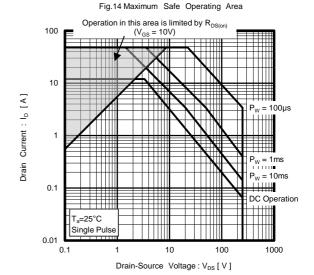


Fig.13 Reverse Recovery Time vs. Source Current







Measurement circuits

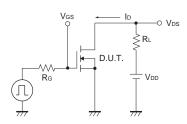


Fig.1-1 Switching Time Measurement Circuit

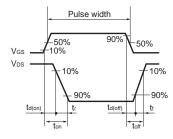


Fig.1-2 Switching Waveforms

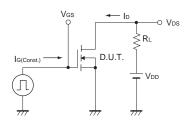


Fig.2-1 Gate Charge Measurement Circuit

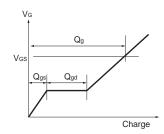


Fig.2-2 Gate Charge Waveform

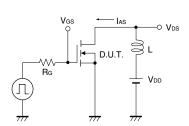


Fig.3-1 Avalanche Measurement Circuit

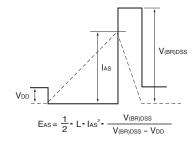


Fig.3-2 Avalanche Waveform

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